CLAIMS: *Please amend the claims according to the status designations in the following list, which contains all claims that were ever in the patent application, with the text of all active claims.*

What I claim are:

1. (Currently amended) A semiconductor device, comprising

   a substrate with texture on the top surface of said substrate, and

   an epitaxial layer comprising an active layer and grown on the top of said texture.

2. The semiconductor device of claim 1, further comprising buffer layer grown in between said epitaxial layer and said texture.

3. The semiconductor device of claim 1, wherein said texture comprising wells and walls.

4. The semiconductor device of claim 3, wherein the width of said walls is in a range of nanometers to micrometers.

5. The semiconductor device of claim 3, wherein the depth of said well is in a range of nanometers to micrometers.

6. (Currently amended)The semiconductor device of claim 3, wherein said wells having a shape of rectangular.

7. The semiconductor device of claim 6, wherein the dimension of said wells is in the range of nanometers to micrometers.

8. (currently amended) The semiconductor device of claim 1, wherein said epitaxial layer of said semiconductor device emits light.

9. (withdraw)

10. (withdraw).

11. (withdraw).

12. (withdraw)

13. (withdraw).

14. (withdraw).

15. (withdraw)

16. (withdraw).

17. (withdraw).

18. (withdraw)

19. (withdraw).

20. (withdraw).

21. (withdraw)

22. (withdraw).

23. (withdraw).

24. (new) The semiconductor device of claim 1, further comprises a second texture formed on the top of said epitaxial layer.

25. (new) The semiconductor device of claim 24, further comprises a second epitaxial layer grown on the top of said second texture and comprising a second active layer.

26. (new) The semiconductor device of claim 25, further comprising a second buffer layer grown in between said second epitaxial layer and said second texture.